Type L # Hits	Hits		Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	Er ro rs
L1 8 transistor\$1) or (thin USPAT; U; EPO; JPO; transistor\$1) or (thin-film-transistor\$1) IBM_TDB	TFT or "TFT" 6413 adj film\$1 adj transistor\$1) c (thin-film-tran	TFT or "TFT" adj film\$1 adj transistor\$1) c (thin-film-tran	r (thin istor\$1)	S-PGPUB;	2004/09/24 09:47			0
BRS L2 6522 stress\$2	22	stress\$2		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:49			0
BRS L3 517 1 with 2		1 with 2		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:26			0
(insulat\$4 or dielec or oxide\$1 or nitric same power same L4 pressure same (electrode\$1 near5 interval\$2) same continuous\$2	(insulat\$4 or di or oxide\$1 or n same power sar pressure same (electrode\$1 ne interval\$2) sam continuous\$2	(insulat\$4 or di or oxide\$1 or n same power sar pressure same (electrode\$1 ne interval\$2) sam continuous\$2	tric Je)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 11:38			0
BRS L5 2029 substrate\$1 or v	substrate\$1	substrate\$1	or wafer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:49		·	0

	Type L#	L #	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	Er ro rs
9	BRS L6	F. C.	4000	$\begin{vmatrix} 4000 \\ 8 \end{vmatrix}$ 2 with (1 or 5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:31			0
7	BRS	<i>L7</i>	1693	1693 6 and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24			0
∞	BRS	Ľ§	2896 427	power\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:39			0
6	BRS	F)	3243 587	pressure\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:39			0
10	BRS	L10	1751	BRS L10 2 interval\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:40			0

	Type L#	L #	Hits	Search Text	DBs	Time Stamp	Comme Definit nts	Error Definit ion
<u> </u>	BRS	5	1133	(8 or 9 or 10) with (chang\$4 or distort\$4 or alter\$6 or modif\$5 or vary or var\$5 or adjust\$4) with (continu\$6 or nonstop\$4 or non-stop\$4 or constant\$4 or incessant\$3 or always or endless\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24		
	BRS L12 39	L12	39	11 and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:46		
<u> </u>	BRS	L13	6530 1	TFT or TFTs or "TFT" 6530 films) adj (transistor or transistors)) or (thin-film-transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:49		
<u> </u>	3RS	L14	2029 151	BRS L14 2029 substrate or substrates 151 or wafer or wafers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:49		

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Er t ro rs

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Type L#	# T	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	ro rs
BRS	L15	6619	BRS L15 6619 stress or stresses or stressing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:50			0
BRS	L16	BRS L16 5	15 with (13 or 14)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:51			. 0
BRS	L17	1752	BRS L17 1752 16 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:51			0
BRS	L18 39	39	11 and 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:52			0

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	Hits	Hits			DBs	Time Stamp	Comme Befinit ro	Error Definit ion	Er ro rs
(8 or 9 or 10) same (chang\$4 or distort\$4 or alter\$6 or modif\$5 or vary or var\$5 or adjust\$4) same adjust\$4) same (continu\$6 or non-stop\$4 or non-stop\$4 or constant\$4 or incessant\$3 or always or endless\$2)	(8 or 9 or 10, (chang\$4 or 0 or alter\$6 or vary or var\$5 adjust\$4) sar 2275 (continu\$6 or non-stop\$4 or non-stop\$4 or non-stop\$4 or non-stop\$4 or endless\$2) or endless\$2	(8 or 9 or 10, (chang\$4 or or alter\$6 or var\$5 adjust\$4) sar 3275 (continu\$6 o nonstop\$4 or non-stop\$4 or non-stop\$4 or endless\$2) or endless\$2)	(8 or 9 or 10, (chang\$4 or or alter\$6 or var\$5 adjust\$4) sar (continu\$6 or non-stop\$4 or non-stop\$4 or constant\$4 or incessant\$3 cor endless\$2)	10) same or distort\$4 or modif\$5 or r\$5 or \$5 or \$1 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24			0
BRS L20 1892 dielectric or oxide\$1 or nitride or oxynitride or oxynitride or oxynitride or oxynitride or oxy-nitride or silicon)	L20 1892 dielectric or o nitride or oxy oxy-nitride or oxy	11 with (insuldielectric or o nitride or oxy oxy-nitride or	11 with (insul dielectric or o nitride or oxy oxy-nitride or		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:45			0
BRS L21 34 13 and 20			13 and 20		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 10:45			0
BRS L22 3282 (chang\$4 or alter\$6 or modif\$5 or adjust\$4) with continu\$6	(8 or 9 or 10) 2282 (chang\$4 or 8 6 modif\$5 or a with continu\$	(8 or 9 or 10) 3282 (chang\$4 or 6 modif\$5 or a with continu\$	(8 or 9 or 10) (chang\$4 or a modif\$5 or a with continu	with alter\$6 or djust\$4) \$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24			0

09/24/2004, EAST Version: 1.4.1

	Type L#	L#	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	ro rs
23	BRS L23 121	L23		22 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24			0
. 24	BRS L24 40	1.24	40	(insulat\$5 or dielectric\$1 or oxide\$1 or nitride\$1 or oxy-nitride\$1) same power same pressure same (electrode\$1 near5 interval\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24			0
25	BRS	1.25	5752	BRS L25 5752 condition\$1 with continuous\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24			0
26	BRS L26 58	L26		25 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24			0

	Type L #			Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	Er ro
	BRS L1		6413 8	TFT or "TFT" or (thin 6413 adj film\$1 adj transistor\$1) or (thin-film-transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24		·	0
2	BRS L2	1.2	6522	stress\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:49			0
3	BRS L3		517	1 with 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:26			0
4	BRS	. 4		(insulat\$4 or dielectric or oxide\$1 or nitride) same power same pressure same (electrode\$1 near\$ interval\$2) same continuous\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24	•,		0
\$	BRS L5		2029 659	substrate\$1 or wafer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:49			0

	Type L#	T #	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	ro rs
9	BRS	Te	4000	L6 $\frac{4000}{8}$ 2 with (1 or 5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:31			0
7	BRS	L7	1693	1693 6 and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:38			0
∞	BRS	L8	2896 427	power\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:39			0
6	BRS	F)	L9 3243 587	pressure\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:39			0
10	BRS	L10	1751	BRS L10 2 interval\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:40			0

09/24/2004, EAST Version: 1.4.1

	Type L #	T #	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	Er ro rs
15	BRS	L15	6619 23	BRS L15 6619 stress or stresses or stressing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:50			0
16	BRŞ	L16	4034 5	BRS L16 4034 15 with (13 or 14)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:51			0
17	BRS	L17	1752	BRS L17 1752 16 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 09:51			0
	BRS L18 39	L18	39	11 and 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 09:52			0

Searc	ch Text	DBs	Time Stamp	Comme Definit ro	Error Definit ion
BRS L19 56 nonstop\$4 or distort\$4 or alter\$6 or modif\$5 or vary or var\$5 or adjust\$4) same adjust\$4) same non-stop\$4 or non-stop\$4 or constant\$4 or incessant\$3 or always or endless\$2)		PGPUB;	2004/09/24		O
BRS L20 1892 dielectric or oxide\$1 or nitride or oxynitride or oxynitride or oxynitride or oxynitride or oxynitride or		S-PGPUB; I;	2004/09/24		0
-13 and 20	USPAT; US- EPO; JPO; DERWENT; IBM_TDB	S-PGPUB; T;	2004/09/24 10:45		0
BRS L22 6 chang\$4 or alter\$6 or modif\$5 or adjust\$4) with continu\$6	USPAT; US- EPO; JPO; DERWENT; IBM_TDB	S-PGPUB; I;	2004/09/24		0

	Type L # Hits	L #	Hits	Search Text	DBs	Time Stamp	Comme Definit ro	Error Er Definit ro ion rs	Er ro
23	BRS L23 121	L23		22 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 11:06			0